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(54) Title: METHOD AND APPARATUS FOR THE SELECTIVE DEPOSITION OF EPITAXIAL GERMANIUM STRESSOR ALLOYS

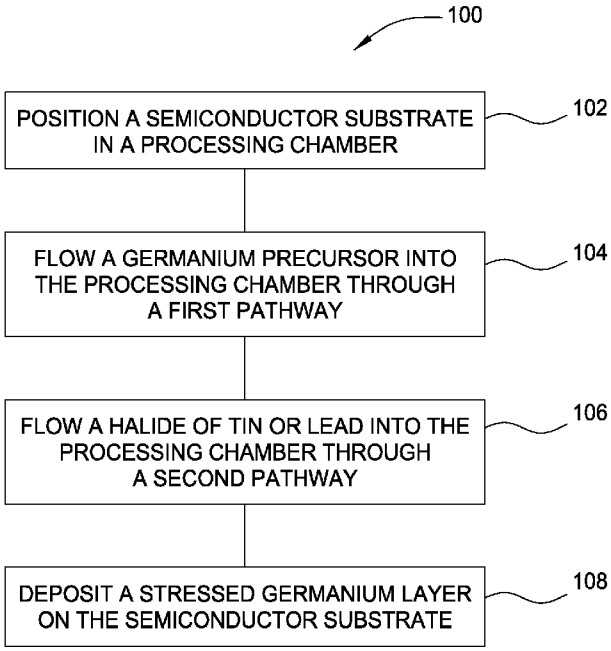


FIG. 1

(57) Abstract: A method and apparatus for forming heterojunction stressor layers is described. A germanium precursor and a metal precursor are provided to a chamber, and an epitaxial layer of germanium-metal alloy formed on the substrate. The metal precursor is typically a metal halide, which may be provided by subliming a solid metal halide or by contacting a pure metal with a halogen gas. The precursors may be provided through a showerhead or through a side entry point, and an exhaust system coupled to the chamber may be separately heated to manage condensation of exhaust components.

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